HL6504FM

Visible High Power Laser Diode for DVD-RAM

HITACHI

ADE-208-825 (Z)
1st Edition
Nov. 1999

Description

The HL6504FM is a 0.66 μm band AlGaInP laser diode (LD) with a multi-quantum well (MQW) structure. It is suitable as a light source for large capacity optical disc memories, such as DVD-RAM, and various other types of optical equipment.

Hermetic sealing of the small package (ϕ 5.6 mm) assures high reliability.

Application

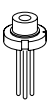
- Optical disc memories
- Optical equipment

Features

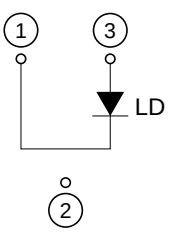
- High output power : 50 mW (CW)
- Visible light output : λp = 664 nm Typ
- Small package : ϕ 5.6 mm
- Low astigmatism : 5 μm Typ (P_O = 5 mW)

Internal Circuit

Package Type
• HL6504FM: FM



Internal Circuit



Hitachi semiconductor

Absolute Maximum Ratings (T_C = 25°C)

Item	Symbol	Value	Unit
Optical output power	P_O	50	mW
Pulse optical output power	$P_{O(pulse)}$	70 *	mW
Laser diode reverse voltage	$V_{R(LD)}$	2	V
Operating temperature	Topr	–10 to +60	°C
Storage temperature	Tstg	–40 to +85	°C

Note: Pulse condition : Pulse width = 100 ns, duty = 50%

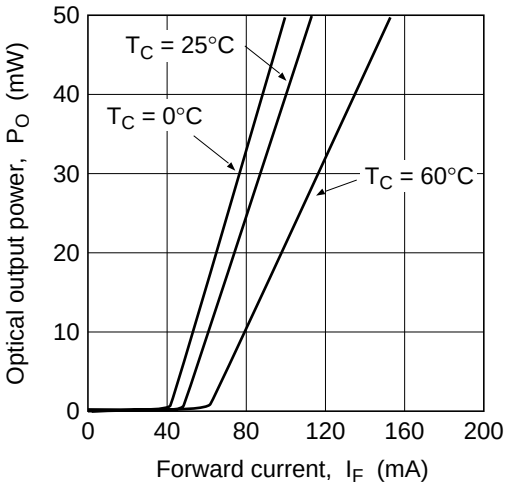
Optical and Electrical Characteristics (T_C = 25°C)

Items	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical output power	P_O	50	—	—	mW	Kink free *
Pulse optical output power	$P_{O(pulse)}$	70	—	—	mW	Kink free *
Threshold current	Ith	30	45	60	mA	—
Operating current	Iop	—	115	135	mA	P_O = 50 mW
Operating voltage	V_{OP}	2.1	2.6	3.0	V	P_O = 50 mW
Beam divergence parallel to the junction	θ//	7	8.5	11	deg.	P_O = 50 mW
Beam divergence parpendicular to the junction	θ⊥	18	21	26	deg.	P_O = 50 mW
Asitgmatism	A_S	—	5	—	μm	P_O = 5 mW, NA = 0.55
Lasing wavelength	λp	655	664	667	nm	P_O = 50 mW

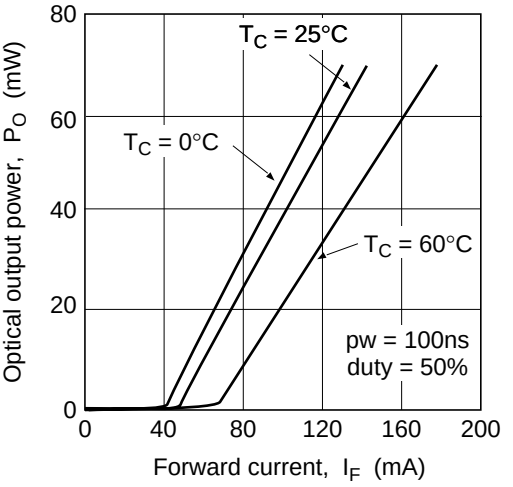
Note: Kink free is confirmed at the temperature of 25°C.

Typical Characteristic Curves

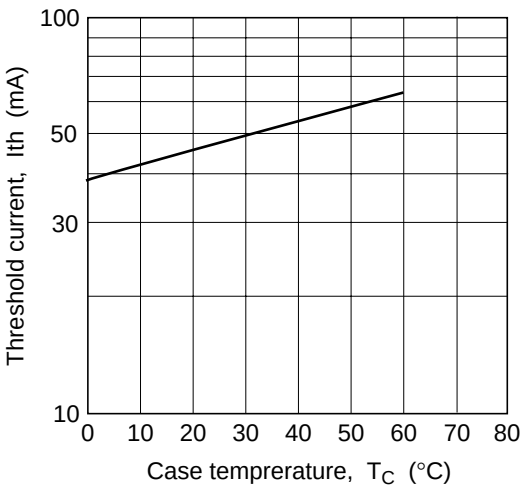
Optical Output Power vs.
Forward Current



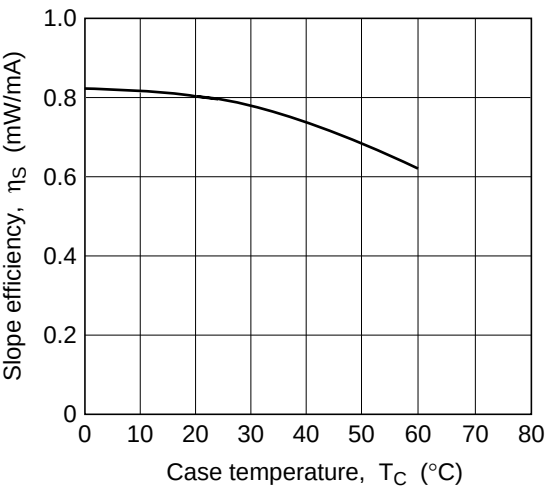
Pulse Optical Output Power vs.
Forward Current



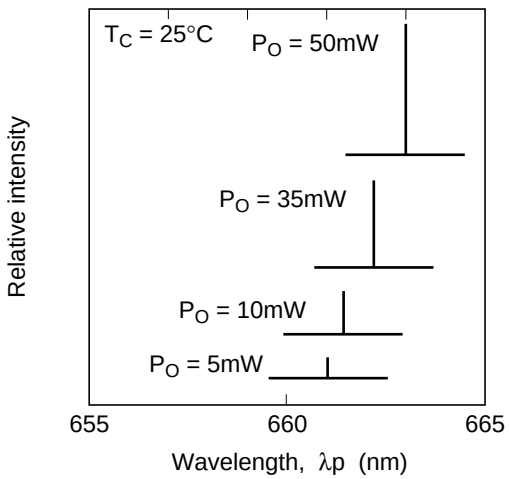
Threshold Current vs.
Case Temperature



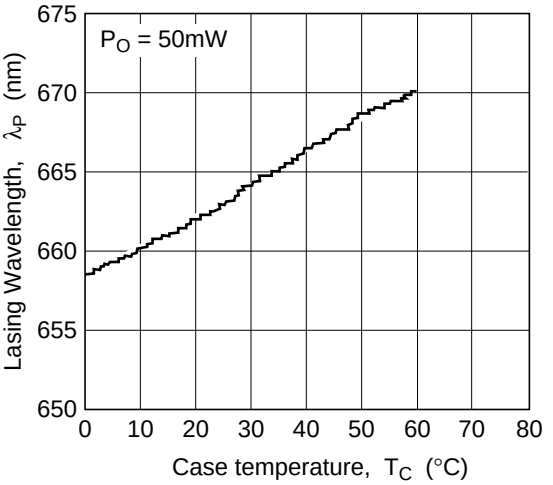
Slope Efficiency vs.
Case Temperature



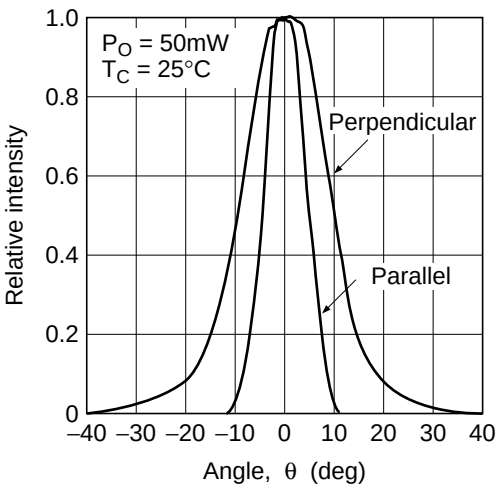
Lasing Spectrum



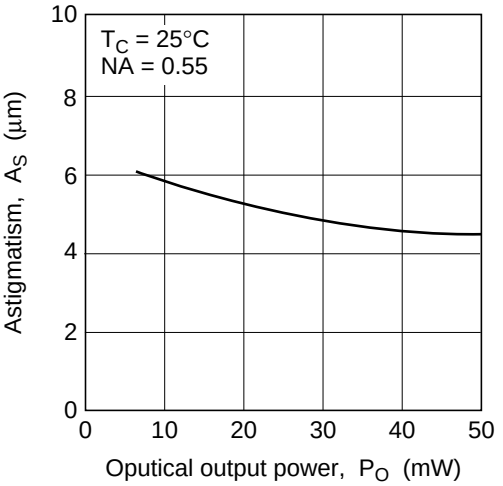
Wavelength vs.
Case Temperature



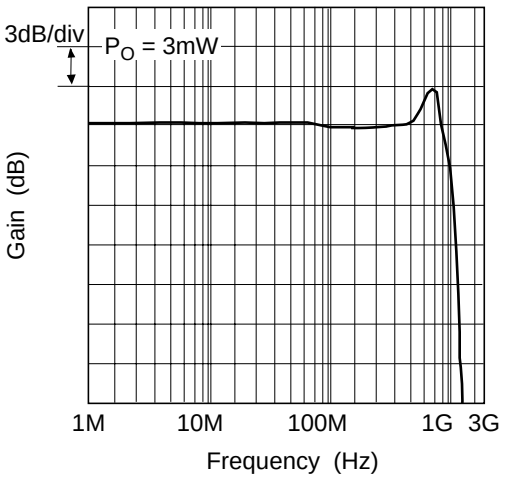
Far Field Pattern



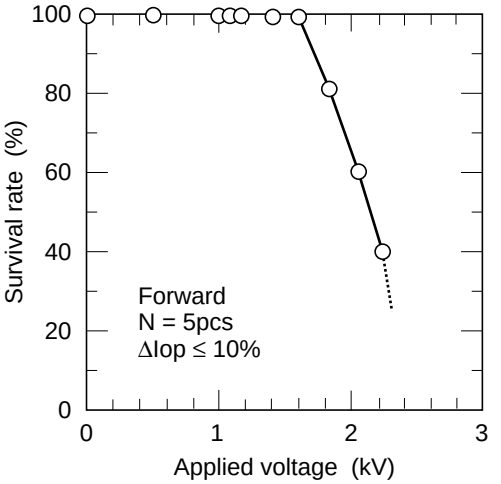
Astigmatism vs.
Optical Output Power



Frequency Response

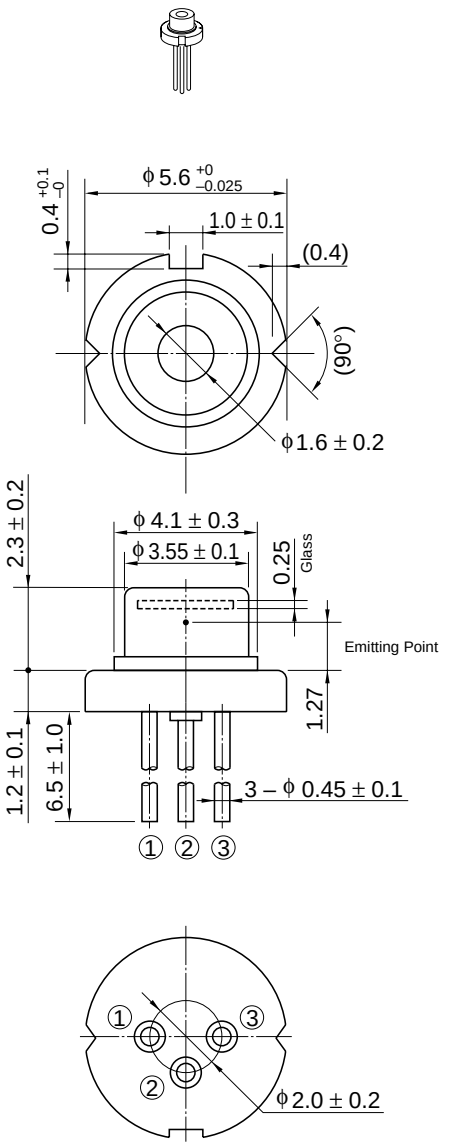


Electrostatic Destruction (MIL standard)



Package Dimensions

Unit: mm



Hitachi Code	LD/FM
JEDEC	—
EIAJ	—
Weight (reference value)	0.3 g

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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http:semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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Japan : http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX